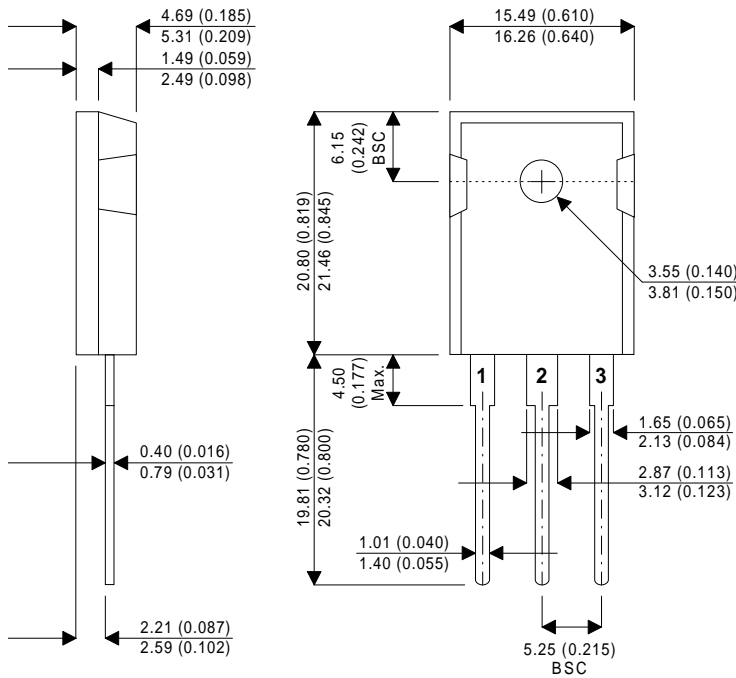


MECHANICAL DATA

Dimensions in mm (inches)



TO-247

Pin 1 – Gate

Pin 2 – Source

Pin 3 – Drain

**P-CHANNEL
POWER MOSFET**

**POWER MOSFETS FOR
AUDIO APPLICATIONS**

FEATURES

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900P & BUZ901P

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}C$ unless otherwise stated)

		BUZ905P	BUZ906P
V_{DSX}	Drain – Source Voltage	-160V	-200V
V_{GSS}	Gate – Source Voltage	$\pm 14V$	
I_D	Continuous Drain Current	-8A	
$I_{D(PK)}$	Body Drain Diode	-8A	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	125W	
T_{stg}	Storage Temperature Range	-55 to 150°C	
T_j	Maximum Operating Junction Temperature	150°C	
$R_{\theta JC}$	Thermal Resistance Junction – Case	1.0°C/W	

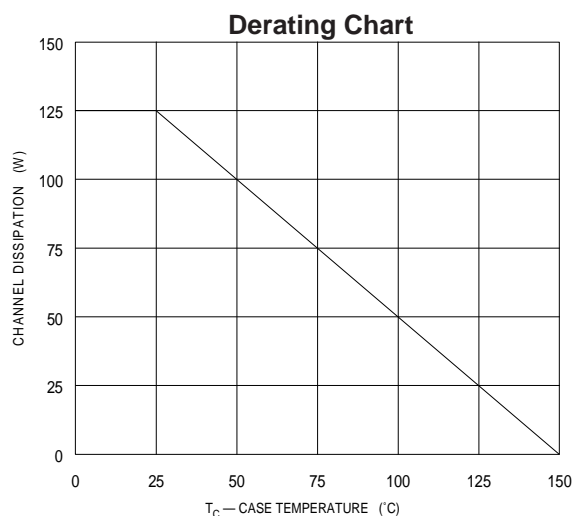
STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX}	Drain – Source Breakdown Voltage	V _{GS} = 10V	BUZ905P	-160			V
		I _D = -10mA	BUZ906P	-200			
BV _{GSS}	Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100µA	±14			V
V _{GS(OFF)}	Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.15		-1.5	V
V _{DS(SAT)*}	Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -8A			-12	V
I _{DSX}	Drain – Source Cut-Off Current	V _{GS} = -10V	V _{DS} = -160V BUZ905P			-10	mA
			V _{DS} = -200V BUZ906P			-10	
yfs*	Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	0.7		2	S

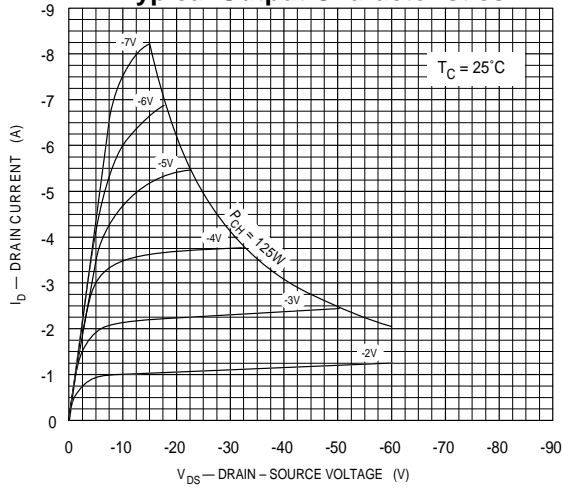
DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C _{iss}	Input Capacitance	V _{DS} = 10V f = 1MHz			734		pF
C _{oss}	Output Capacitance				300		
C _{rss}	Reverse Transfer Capacitance				26		
t _{on}	Turn-on Time	V _{DS} = -20V I _D = -5A			120		ns
t _{off}	Turn-off Time				60		

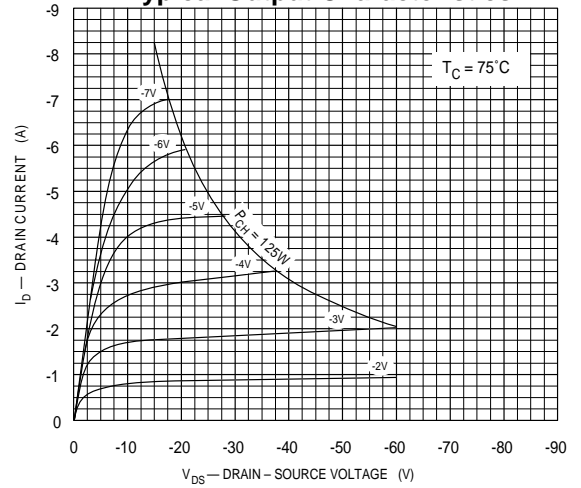
* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.



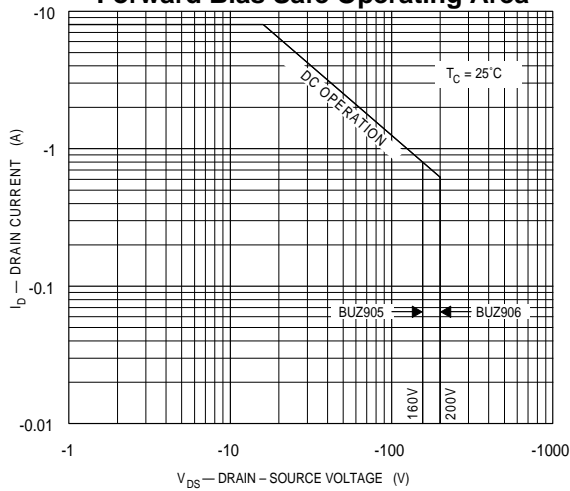
Typical Output Characteristics



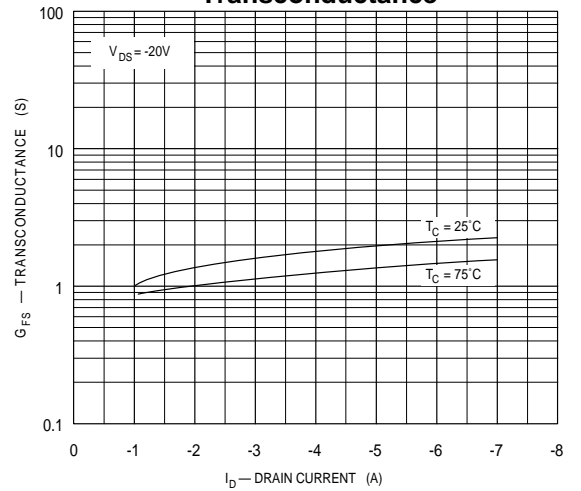
Typical Output Characteristics



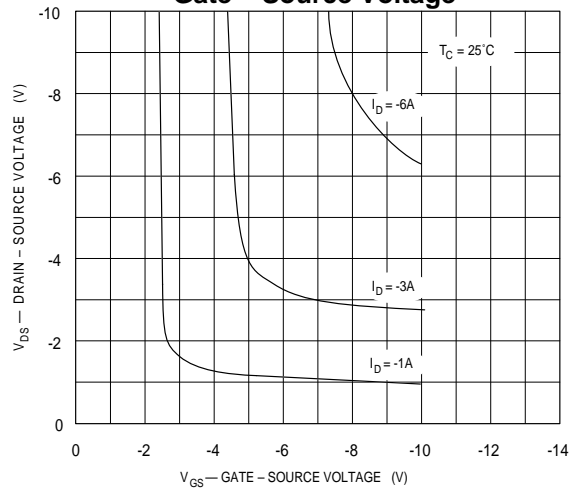
Forward Bias Safe Operating Area



Transconductance



Drain - Source Voltage vs Gate - Source Voltage



Typical Transfer Characteristics

